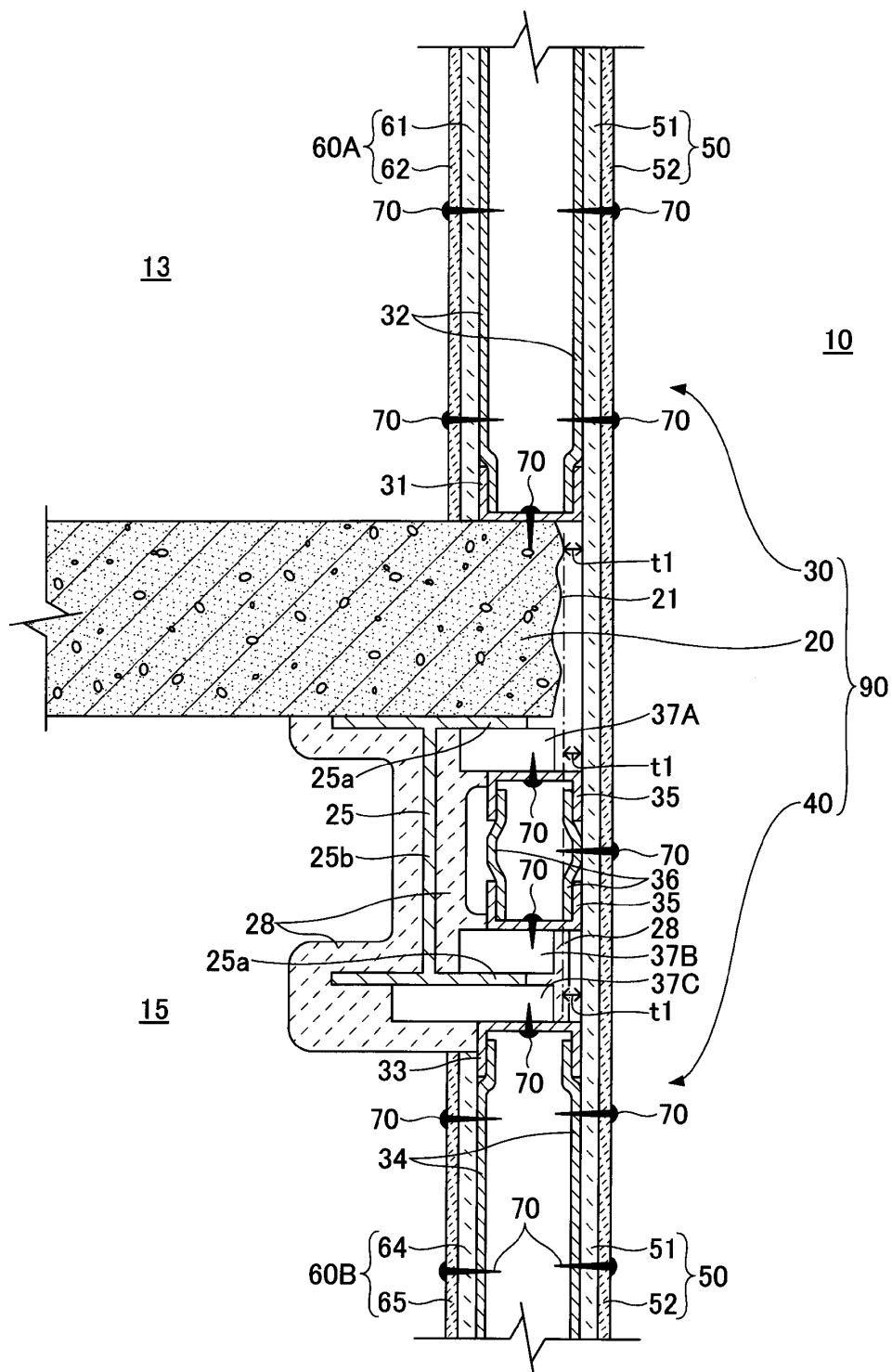
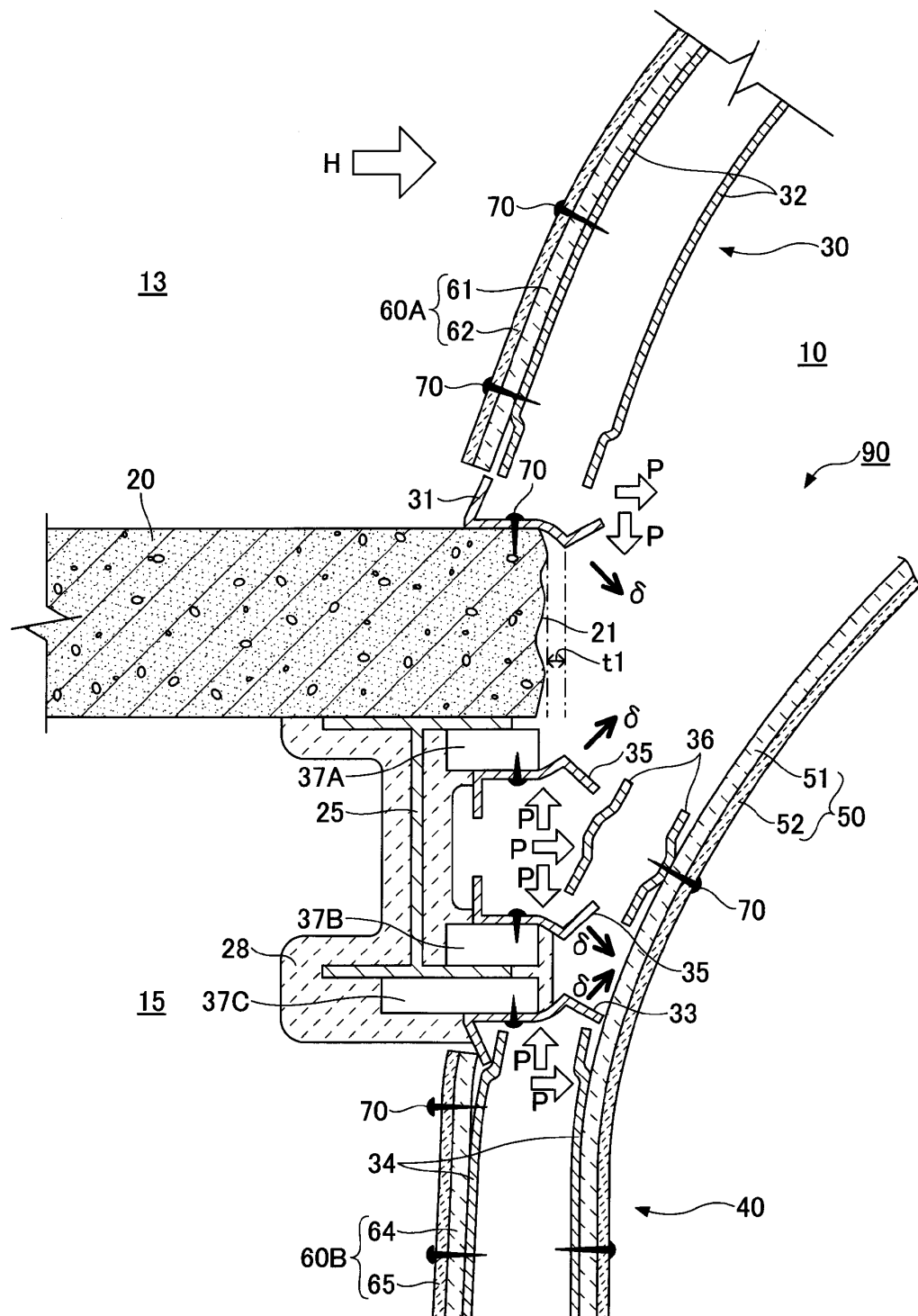


[図1]



[図2]



[図3]

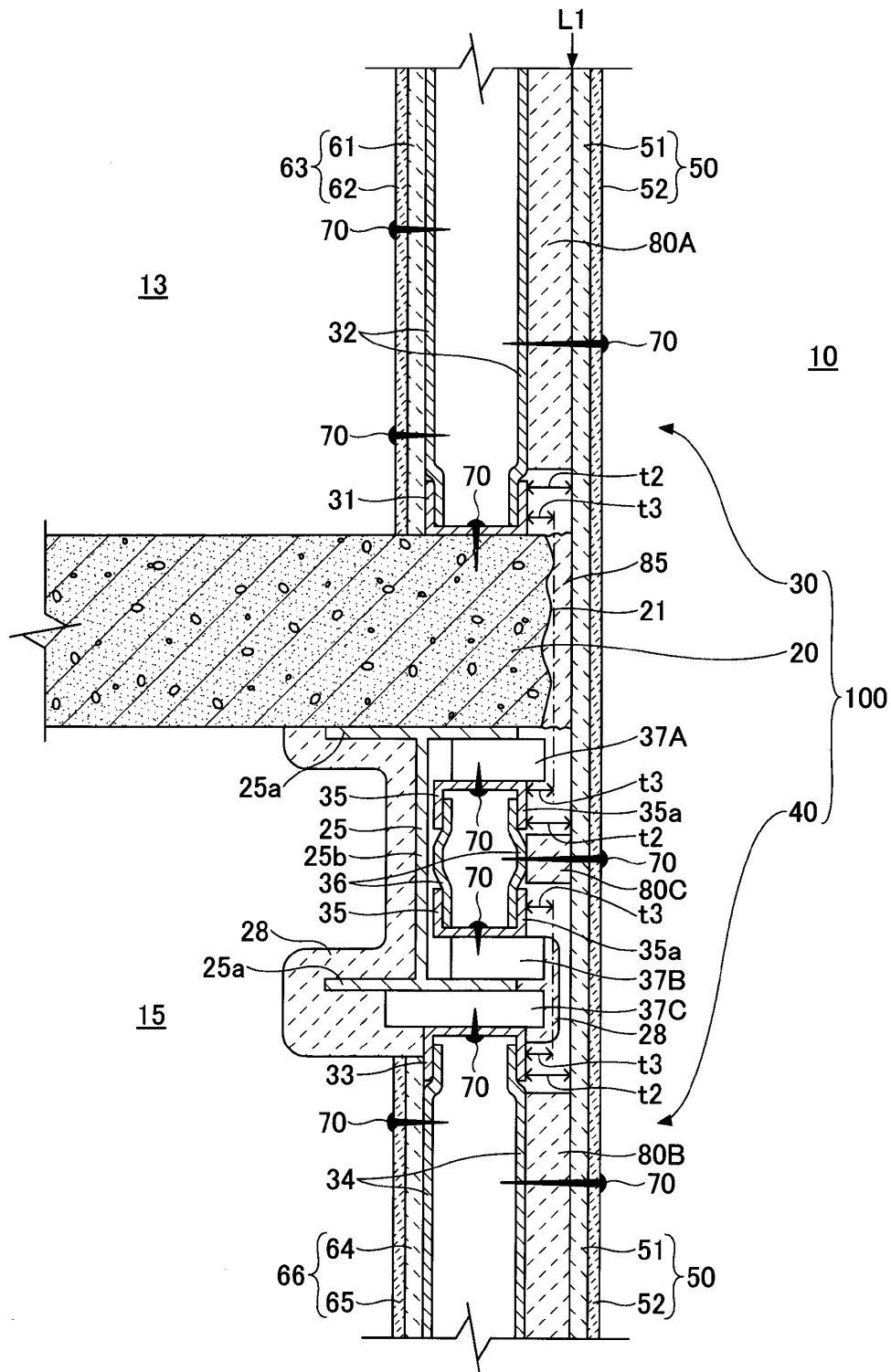
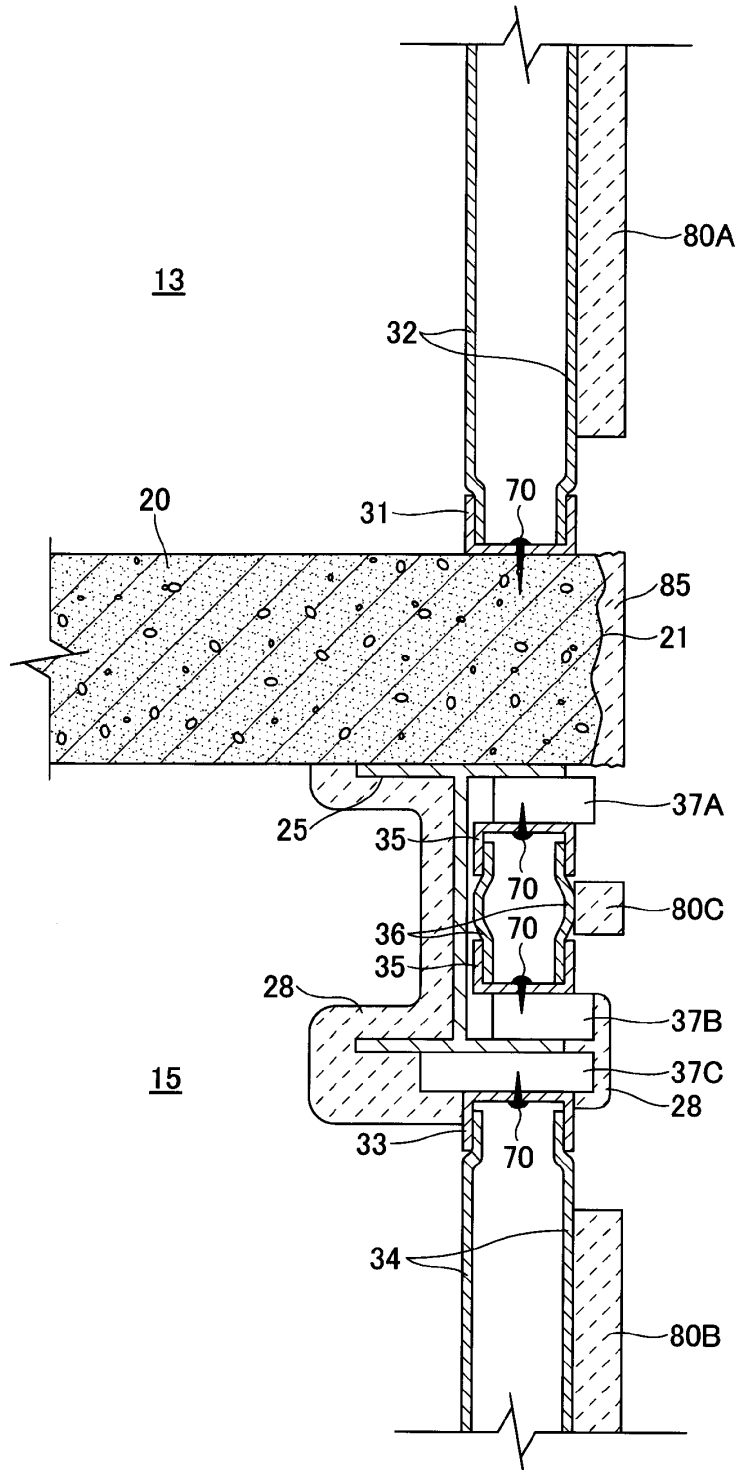


Figure 1 is a cross-sectional view of a semiconductor device. It shows a substrate 13 and a gate stack 15. The substrate 13 has a top surface 20 and a bottom surface 21, with a trench 70 between them. The gate stack 15 is located on the right side of the substrate 13 and includes several layers: 25a, 25b, 35, 36, 37A, 37B, 37C, and 38. The thickness of the gate stack 15 is indicated as L1. The width of the trench 70 is indicated as t2. The distance from the top surface 20 to the bottom surface 21 is indicated as Q. The thickness of the substrate 13 is indicated as t1.

[図5]

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